Abstracts

A High Power Q-Band GaAs Pseudomorphic HEMT Monolithic Amplifier

W. Boulais, R.S. Donahue, A. Platzker, J. Huang, L. Aucoin, S. Shanfield and M. Vafiades. "A High Power Q-Band GaAs Pseudomorphic HEMT Monolithic Amplifier." 1994 MTT-S International Microwave Symposium Digest 94.2 (1994 Vol. II [MWSYM]): 649-652.

A first-pass, three stage monolithic GaAs Pseudomorphic HEMT power amplifier has been developed for use over the 40 GHz to 45 GHz band. The MMIC amplifier delivers 500 to 725 mW at the one dB gain compression point. The associated power gain is 10 to 11 dB and the power added efficiency is 10 to 17 %. Potential applications for this work include communication systems and phased array radars.

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